

**PD1450-35F59**  
InGaAs PIN-Photodiode

PD1450-35F59 is an InGaAs PIN-Photodiode. This PIN-Photodiode is consists of a large chip with 350x350um active area mounted on the TO-46S stem and is hermetical sealed by metal can with flat lens. These devices are designed to be easy of setting up optically with a wide angle of half sensitivity of  $\pm 58^\circ$ .

<Specifications>

1. Product Name: Stem Type Photo-Diode
2. Type Number: PD1450-35F59
3. Chip:
  - Chip Size: 400umx400um
  - Active Area: 350umx350um
4. Package
  - Type: TO-46 Stem
  - Lens: Flat Glass Lens
  - Cap: Nickel Plated

Outer Dimension (Unit:mm)



Absolute Maximum Ratings[Ta=25°C]			
Item	Symbol	Maximum Rated Value	Unit
Reverse Breakdown Voltage	V(BD)R	15	V
Operating Temperature	TOPR	-20 ~ +90	°C
Storage Temperature	TSTG	-30 ~ +100	°C
Soldering Temperature*	TSOL	265	°C

\* Soldering condition must be completed within 3 second at 265 °C.

Electro-Optical Characteristics [Ta=25°C typ.]						
Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Photo Responsibility	RE	VR=0V, λP=1450nm		0.9		A/W
Reverse Photo Current	IL	VR=0V, λP=1450nm	15	28		uA
Reverse Dark Current	ID	VR=3V			100	nA
Spectral Responsibility(Peak)	λP	VR=0V	1000		1600	nm
Half Angle of Sensitivity	θ1/2	VR=0V		±58		Deg.
Total Capacitance	CT	F=1MHz	VR=0V	50		pF
			VR=5V	15		
Rise Time	tr	RL=1kΩ, VR=1V		20		ns
Fall Time	tr			20		

Measured by Epitex's calibrated tool.



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